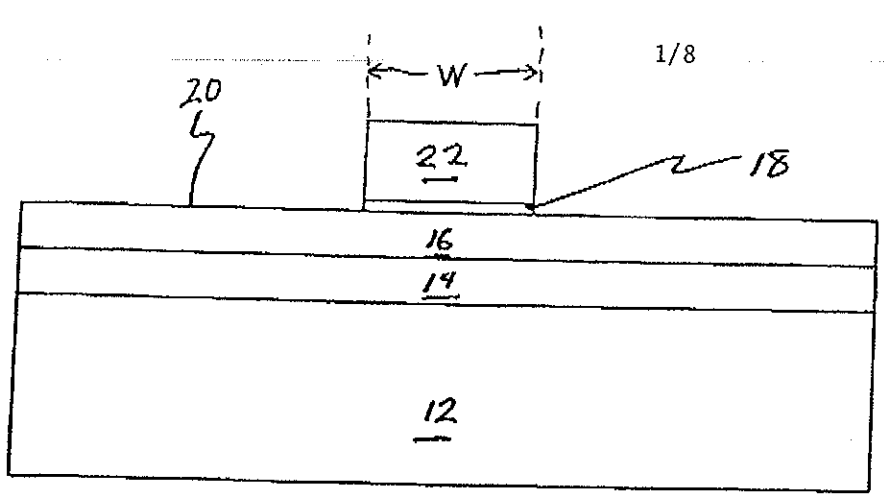


FIG. 1

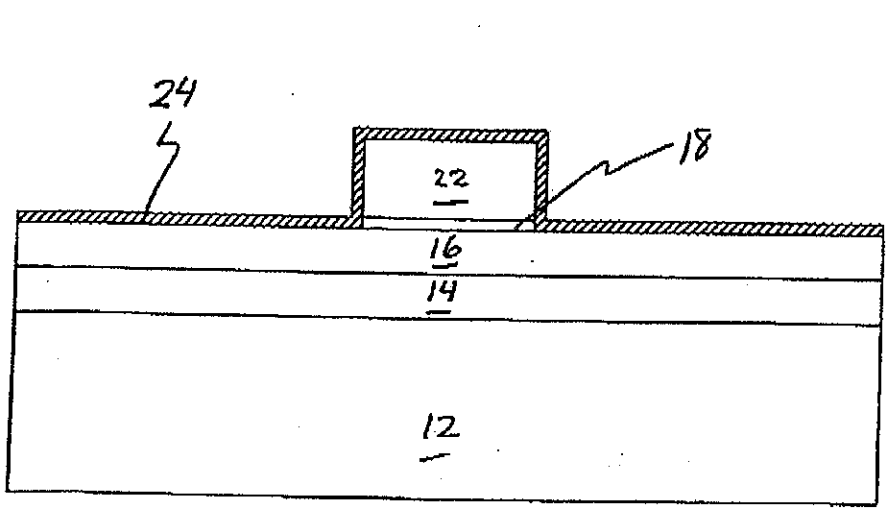


FIG. 2

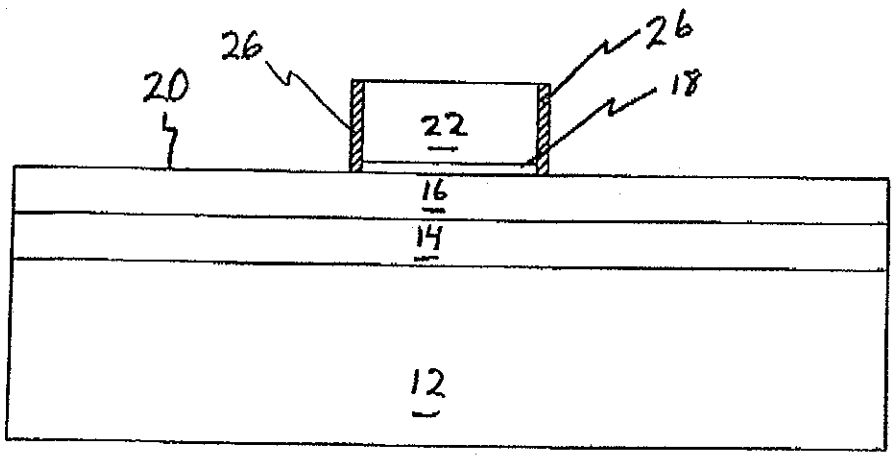


FIG. 3

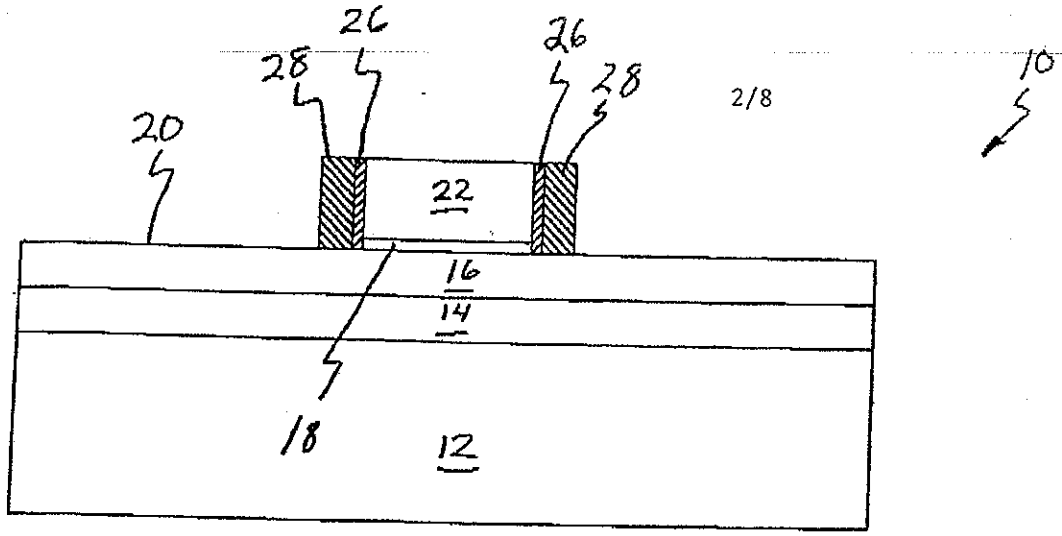


FIG. 4

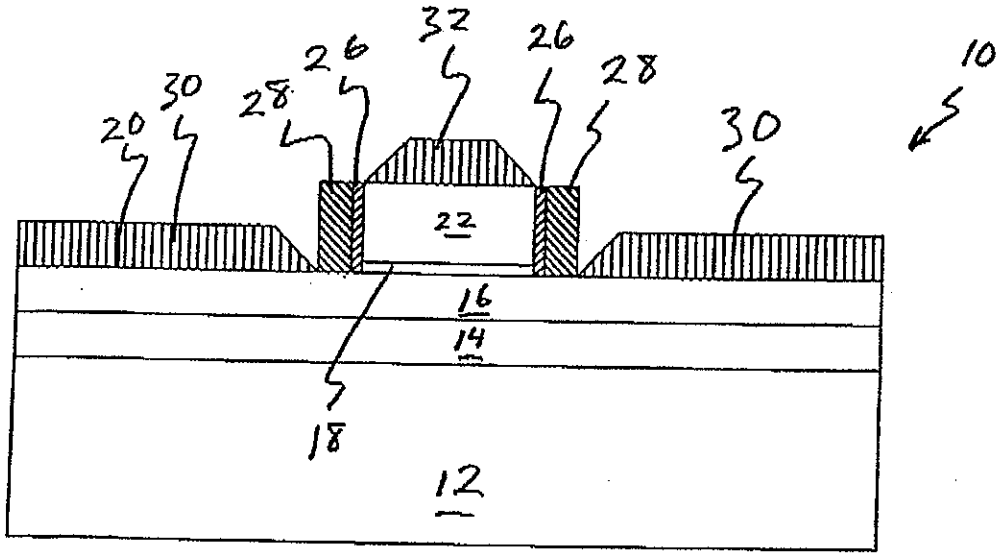


FIG. 5

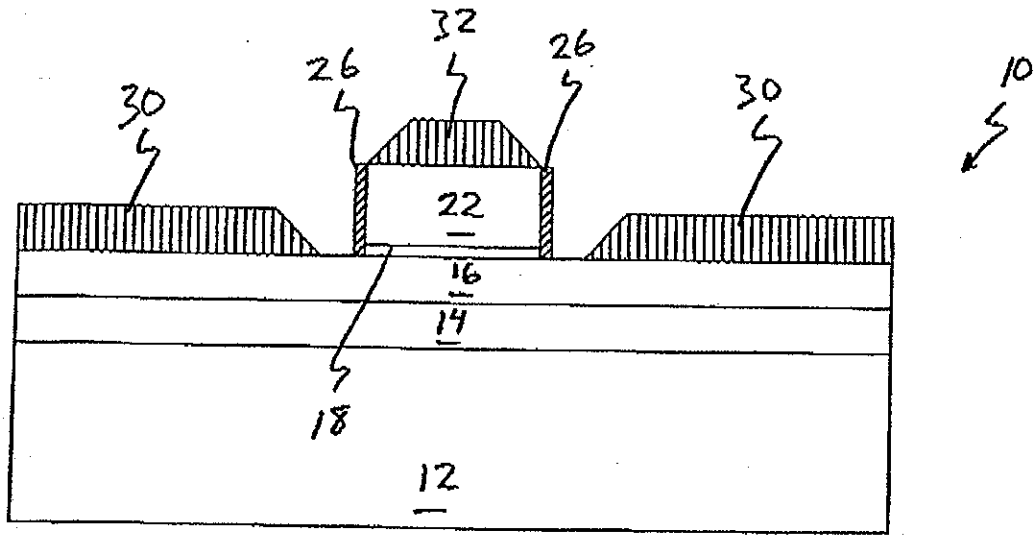


FIG. 6

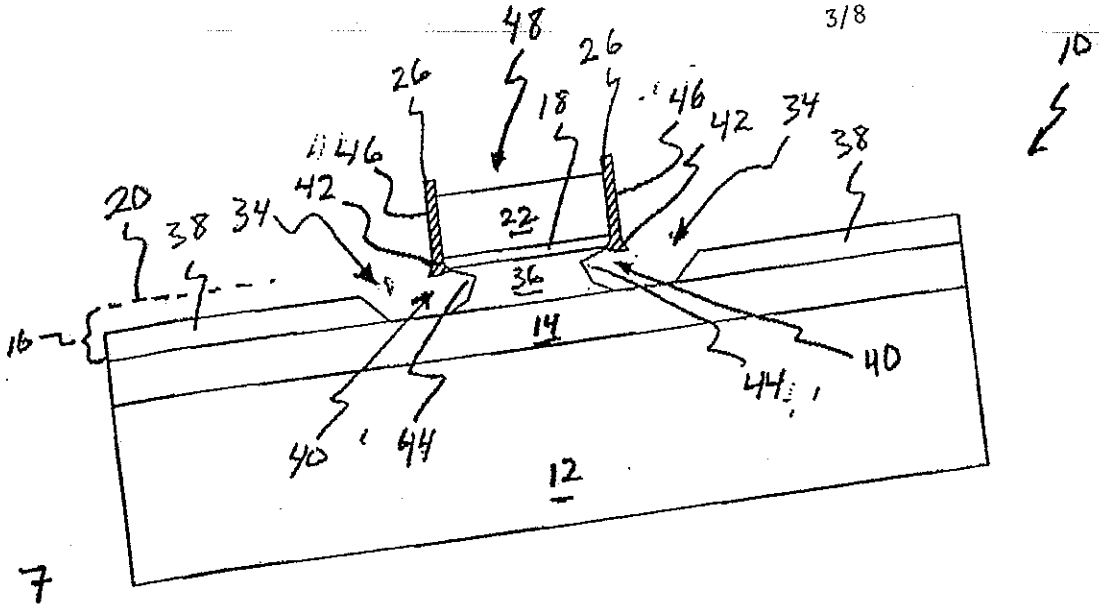


FIG. 7

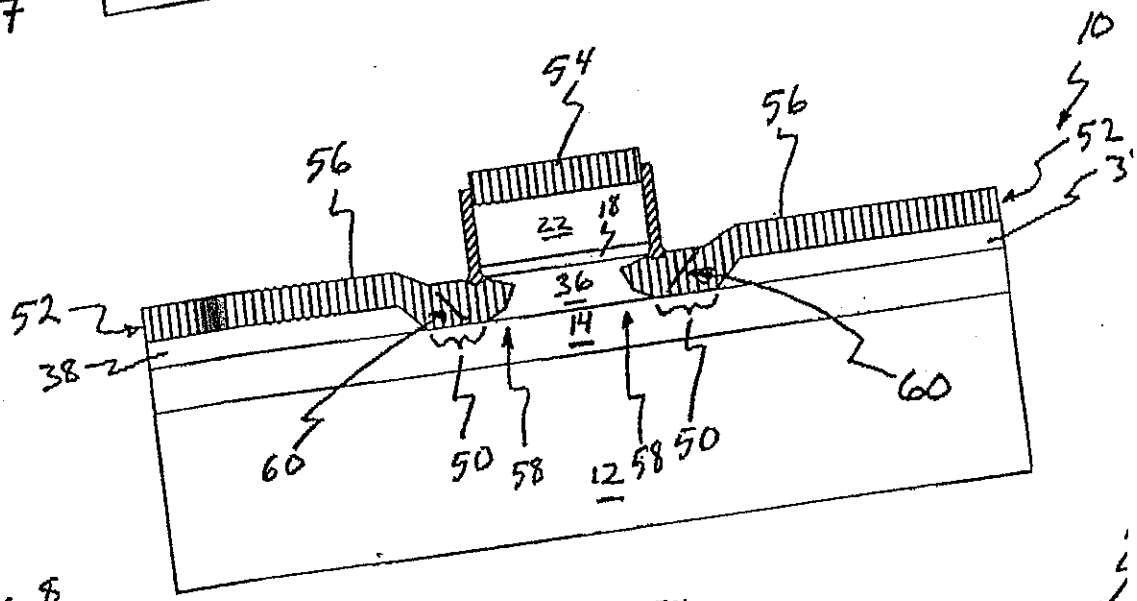


FIG 8

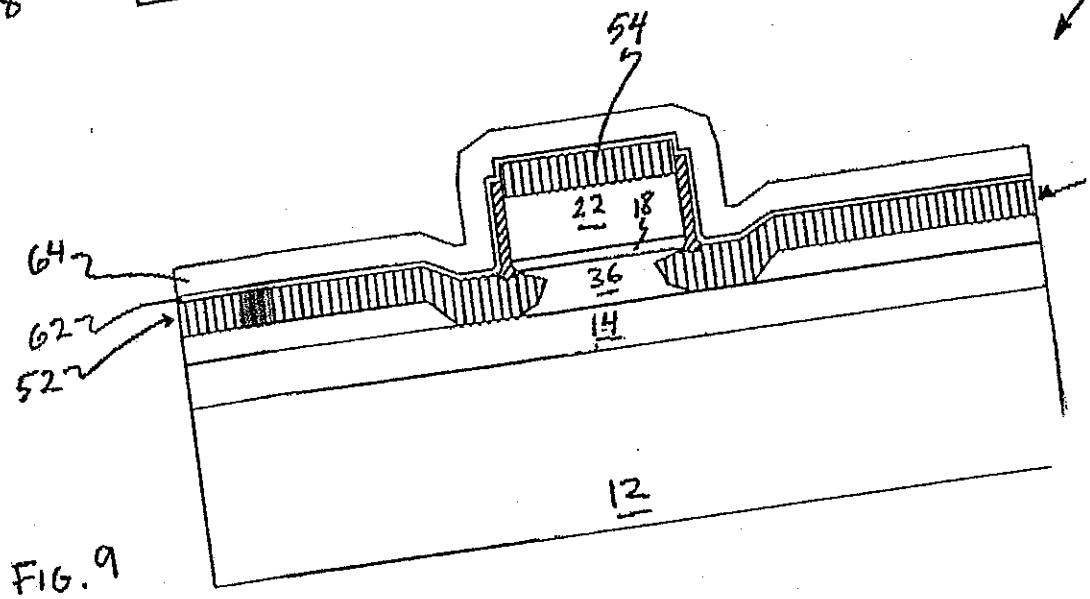


FIG. 9

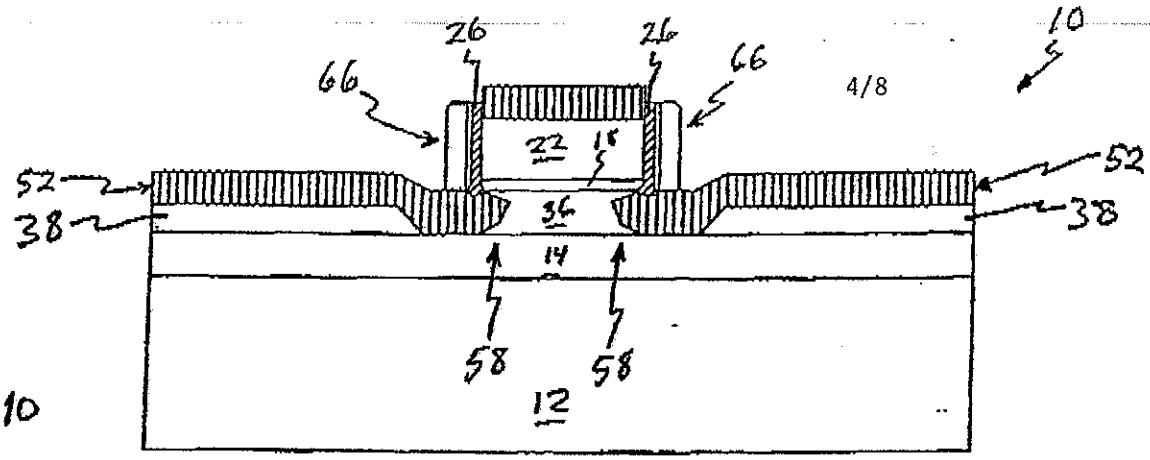

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FIG. 10

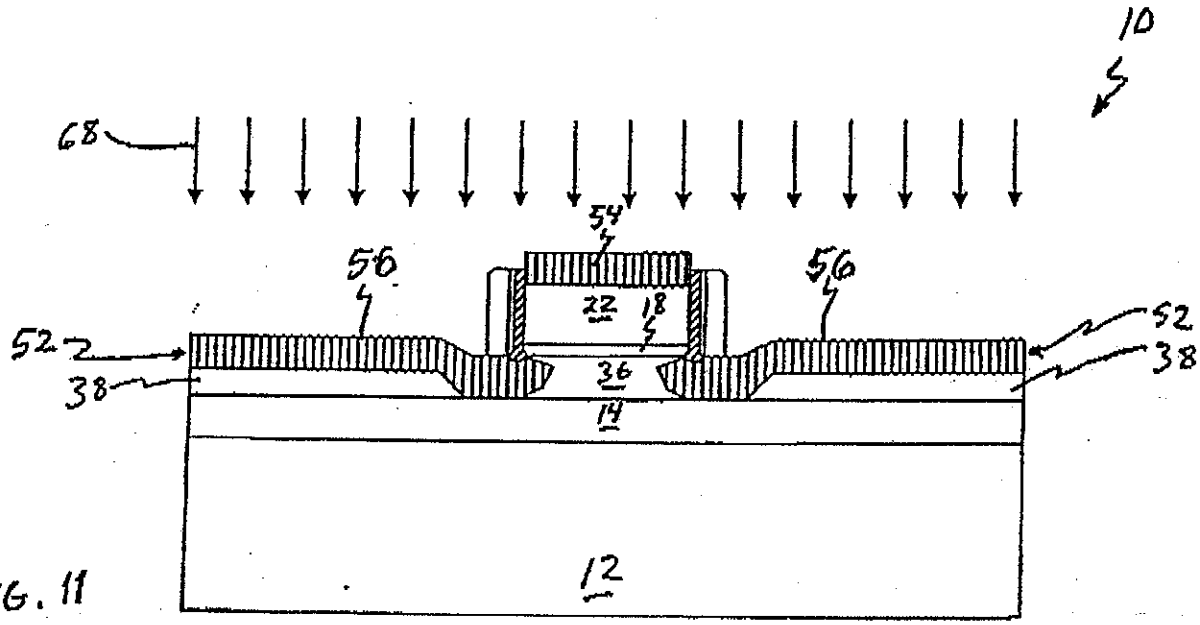

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FIG. 11

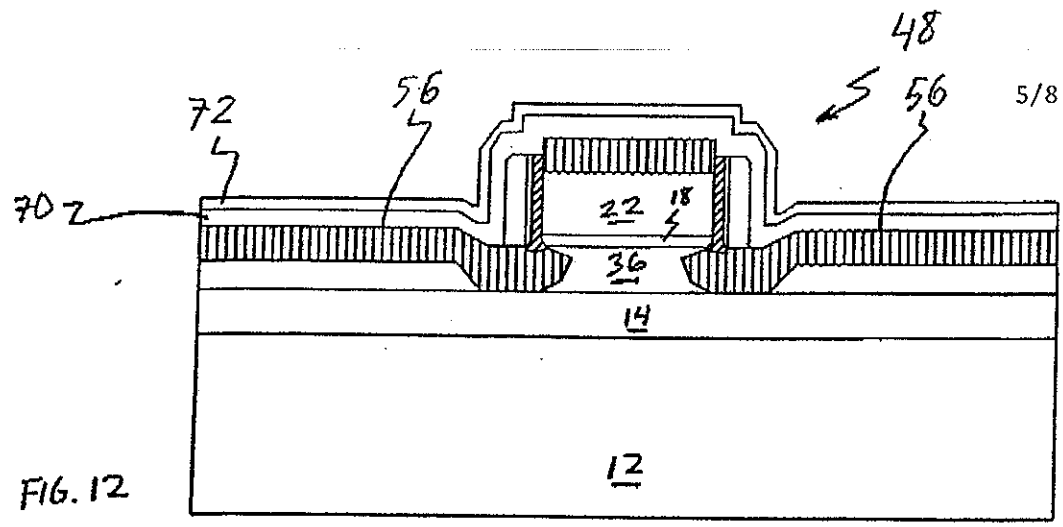


FIG. 12

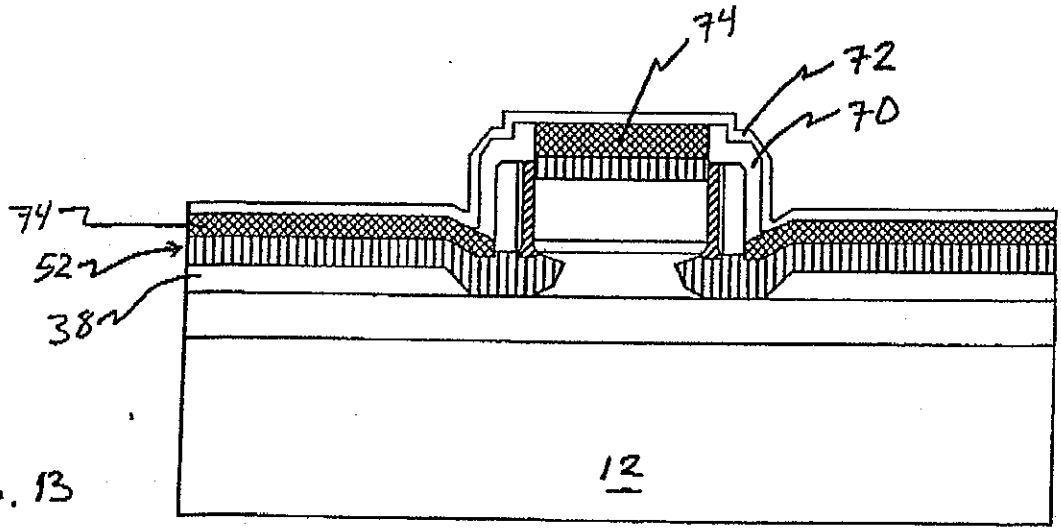


FIG. 13

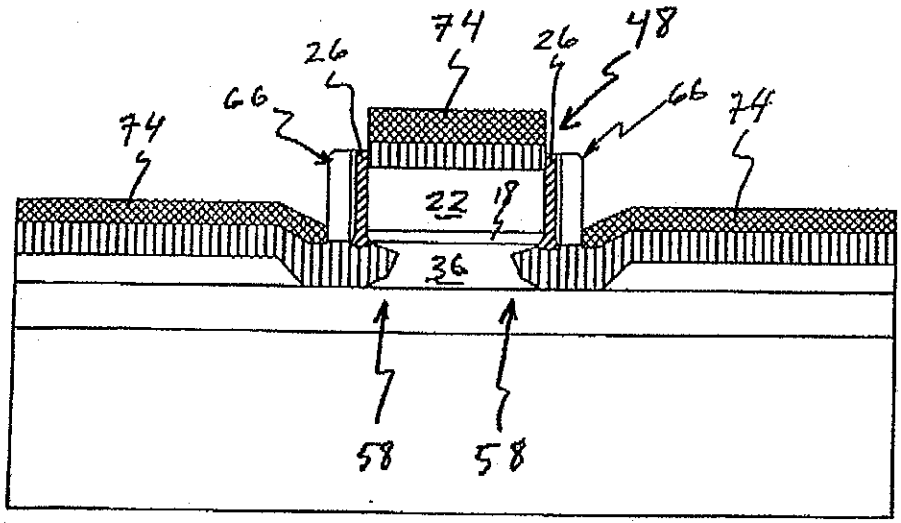


FIG. 14

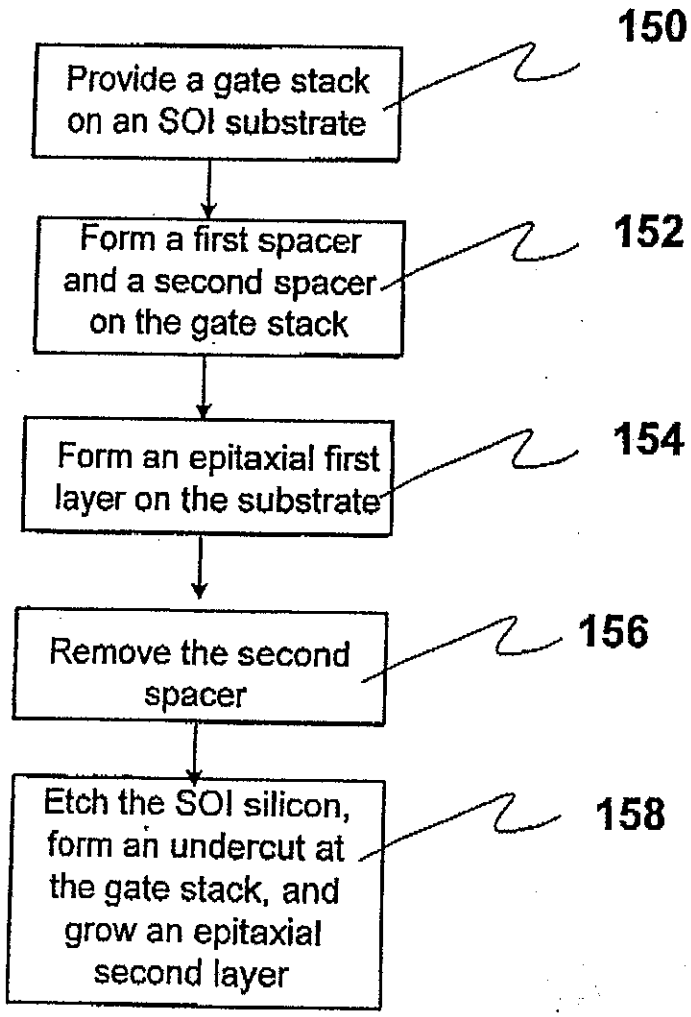

Provide a gate stack on an SOI substrate
150
Form a first spacer and a second spacer on the gate stack
152
Form an epitaxial first layer on the substrate
154
Remove the second spacer
156
Etch the SOI silicon, form an undercut at the gate stack, and grow an epitaxial second layer
158

FIG. 15

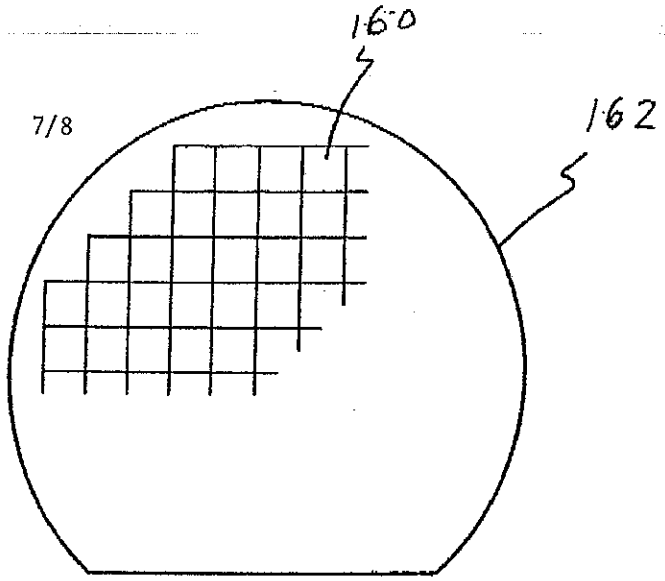


FIG. 16

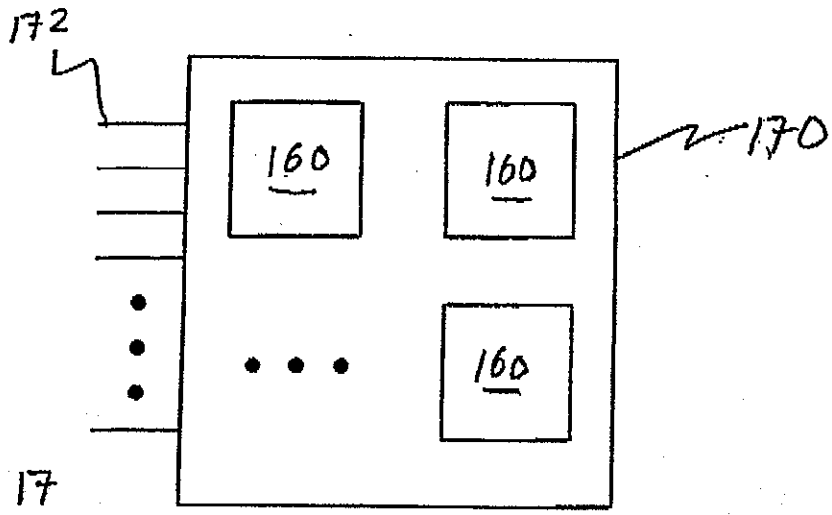


FIG. 17

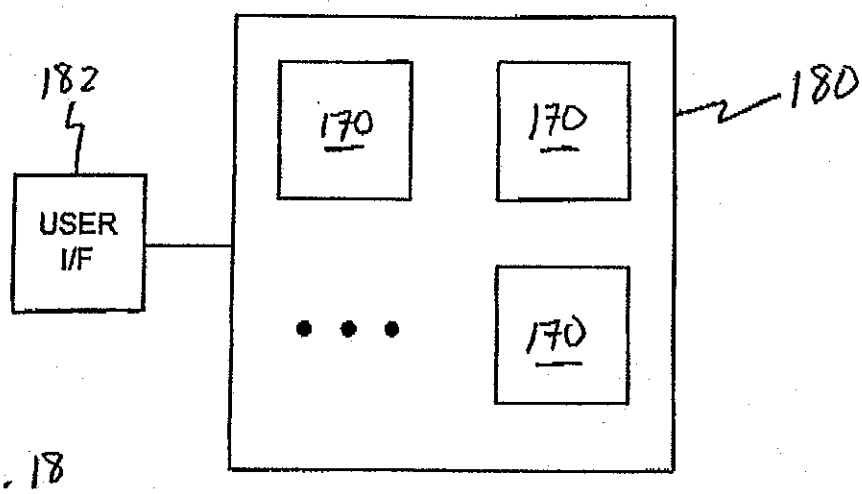


FIG. 18

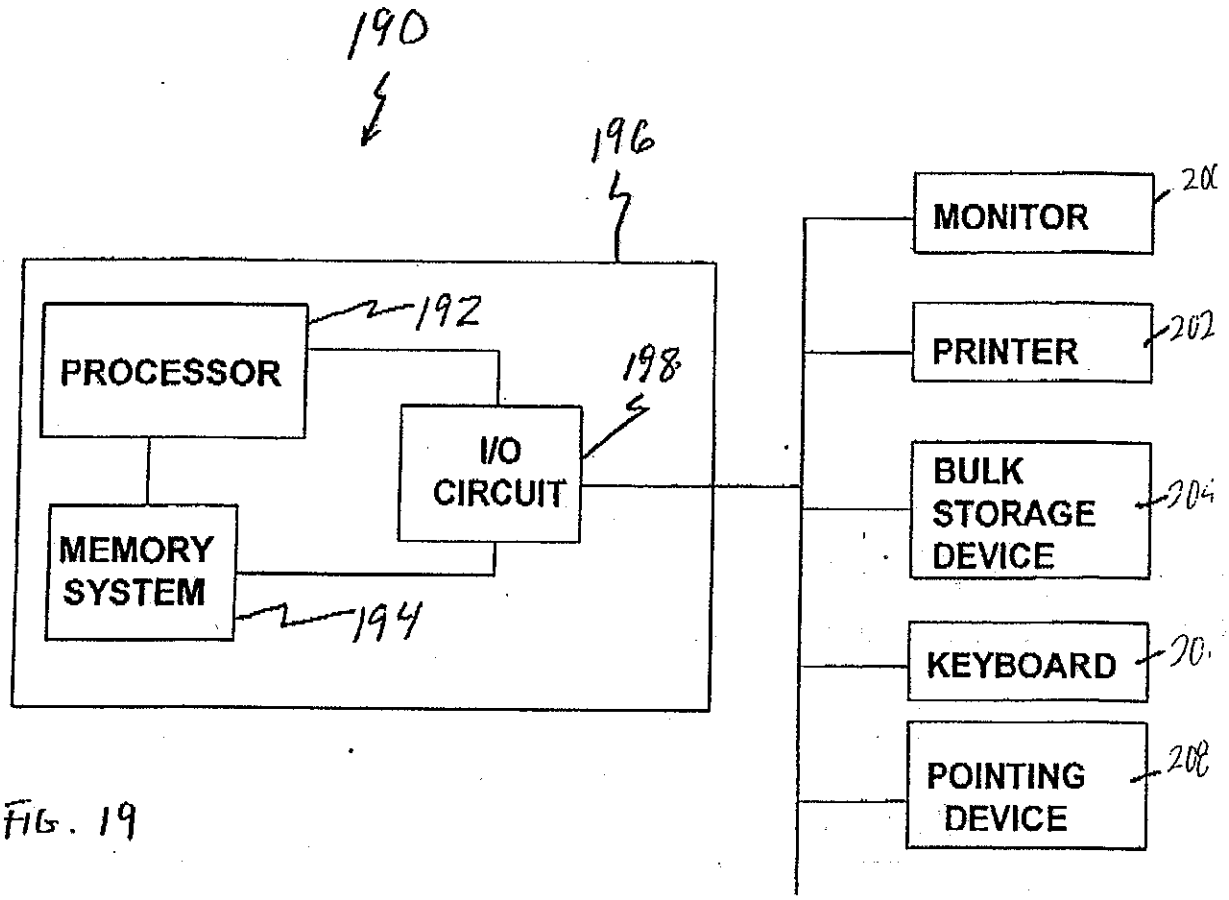

190
196
PROCESSOR
192
198
I/O CIRCUIT
MEMORY SYSTEM
194
MONITOR
20
PRINTER
202
BULK STORAGE DEVICE
204
KEYBOARD
20
POINTING DEVICE
20

FIG. 19